

D3SB10 - D3SB80

SILICON BRIDGE RECTIFIERS

PRV : 100 - 800 Volts

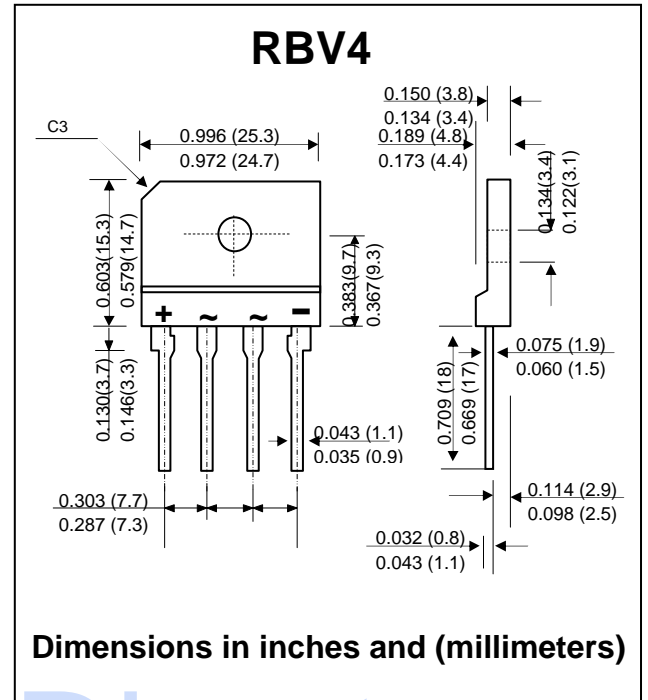
Io : 4.0 Amperes

FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Ideal for printed circuit board
- * Very good heat dissipation
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : Reliable low cost construction utilizing molded plastic technique
- * Epoxy : UL94V-O rate flame retardant
- * Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Polarity symbols marked on case
- * Mounting position : Any
- * Weight : 4.28 grams



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specific.
Single phase, half wave, 60 Hz, resistive or inductive load
For capacitive load, derate current by 20%

RATING	SYMBOL	D3S B10	D3S B20	D3S B40	D3S B60	D3S B80	UNIT
Maximum Reverse Voltage	V _{RM}	100	200	400	600	800	V
Maximum Average Forward Current T _c = 25°C	I _{F(AV)}	4.0					A
Maximum Peak Forward Surge Current	I _{FSM}	120					A
Maximum Forward Voltage per Diode at I _F = 2.0 A	V _F	1.05					V
Maximum Reverse Current at Reverse Voltage	I _R	10					µA
Maximum Reverse Current at Reverse Voltage T _a = 100 °C	I _{R(H)}	100					µA
Operating Junction Temperature Range	T _J	- 40 to + 150					°C
Storage Temperature Range	T _{STG}	- 40 to + 150					°C

RATING AND CHARACTERISTIC CURVES (D3SB10 - D3SB80)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

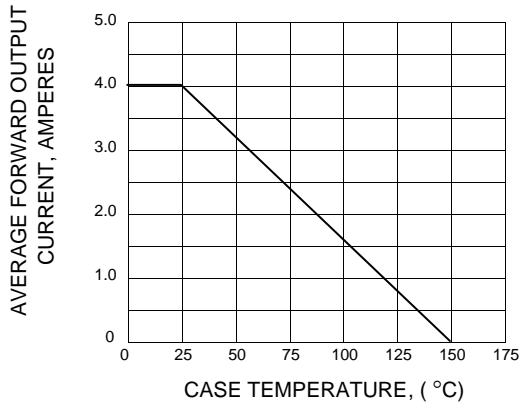


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

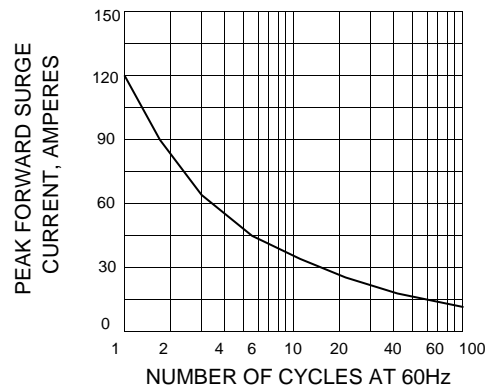


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

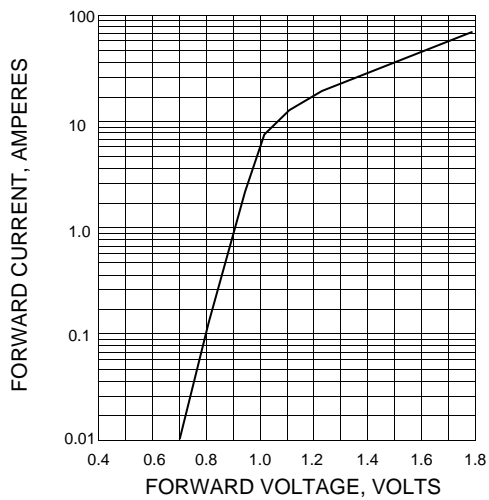


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

